

ABSTRACT

An object of the present invention is to provide a composition for formation of etching stopper layer, which can simultaneously realize dry  
5 etching selectivity and low permittivity, and a production process of a semiconductor device using the same. This object can be attained by a composition for formation of etching stopper layer, comprising a silicon-containing polymer, the silicon-containing polymer contained in  
10 the composition comprising a disilylbenzene structure, and a production process of a semiconductor device comprising forming an etching stopper layer using the composition.